BT151 12A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, BT151 of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference.
It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220B is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	650	V
I_{GT}	≤15	mA

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Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS (T_j=25)

MARKING

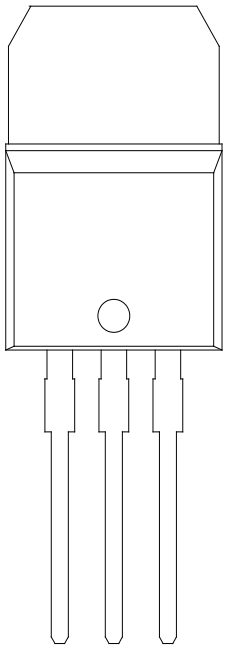


FIG.1: Maximum power dissipation versus RMS on-state current

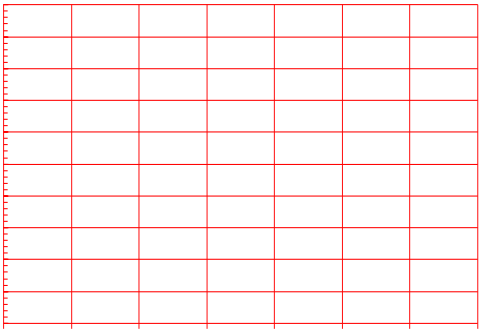
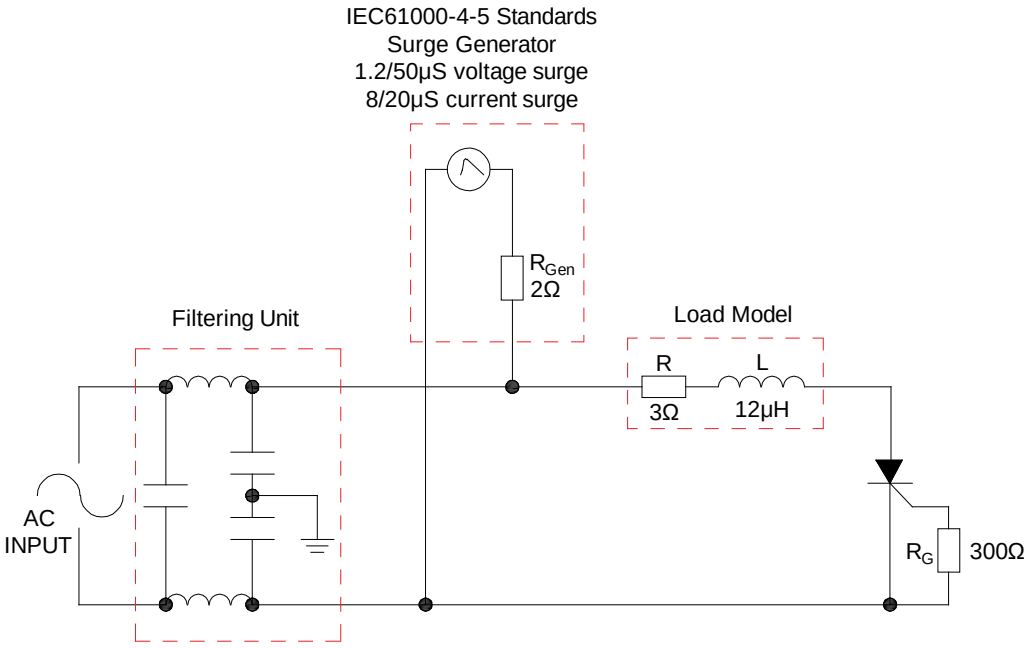


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

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PACKAGE MECHANICAL DATA

